TENTATIVE

Model 325-SF-02 series
Bare Die (Flip chip form, AuSn Pad)

Typical Optical-Electrical Characteristics

(I_F=20mA, T_a=25°C)

Item	Symbol	Unit	325-SF-02-C		
			Min	Typ	Max
Peak Wavelength	λ_p	nm	320	325	330
Radiant Flux	P_o	mW	-	3.5	-
Full Width at Half Maximum	$\Delta\lambda$	nm	-	13	-
Forward Voltage	V_F	V	-	4.9	-

(I_F=50mA, T_a=25°C)

Item	Symbol	Unit	325-SF-02-C		
			Min	Typ	Max
Peak Wavelength	λ_p	nm	320	325	330
Radiant Flux	P_o	mW	-	8.7	-
Full Width at Half Maximum	$\Delta\lambda$	nm	-	13	-
Forward Voltage	V_F	V	-	5.2	-

(*)Peak Wavelength Measurement tolerance is ±3nm.

(**)Radiant Flux Measurement tolerance is ±10%.

Binning is available.

Specification and dimension are subject to change for improvement without notice.

Absolute Maximum Ratings

Item	Symbol	Unit	Value
Forward Current	I_F	mA	50
Junction Temperature	T_J	℃	90
Operating Temperature	T_{OPR}	℃	-30 ～ +85
Storage Temperature	T_{STR}	℃	-40 ～ +85 (No condensation)

⚠ WARNING

- **LEDs emit very strong UV radiation.**
- **Do not look at the LED light with the naked eye or irradiate the skin.**
  UV radiation can harm your eyes and skin.
- **To prevent UV radiation exposure, wear protective eyewear and protective equipment.**
- **If LEDs are embedded in devices, please indicate warning labels against the UV light LED used.**
- **Keep out of reach of children.**

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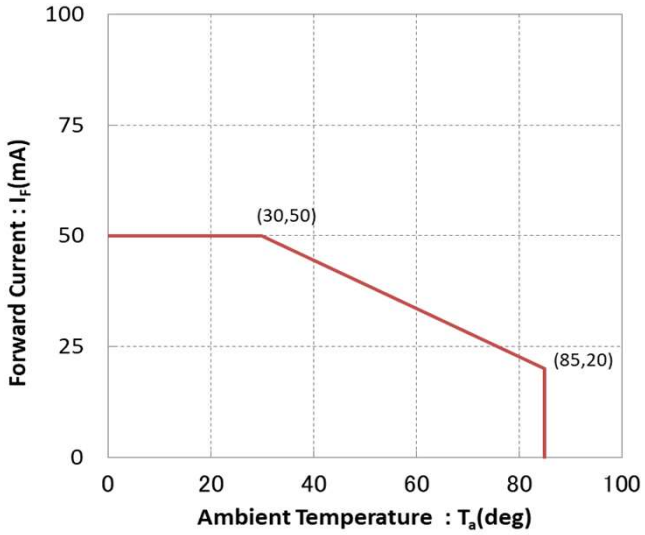
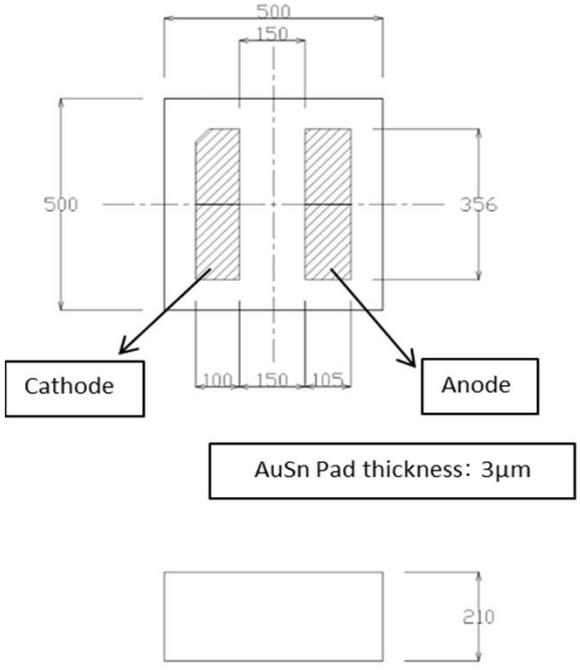
Derating Curve

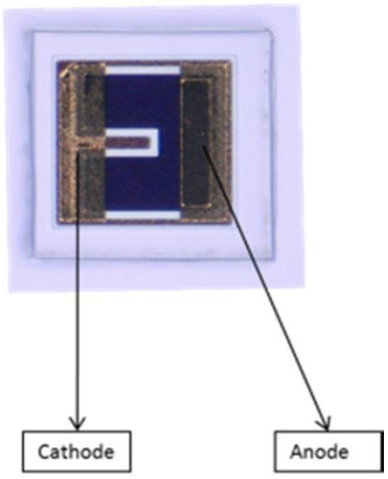


Notes:
Maximum ratings and derating curve strongly depend on assembly materials.
The above ratings and derating curve were determined using AlN submount ,Al substrate and heatsink. Ratings may be different for other materials and enviroment.

Product ID, Physical dimensions and Sample photo

325-SF-02-C Bare die





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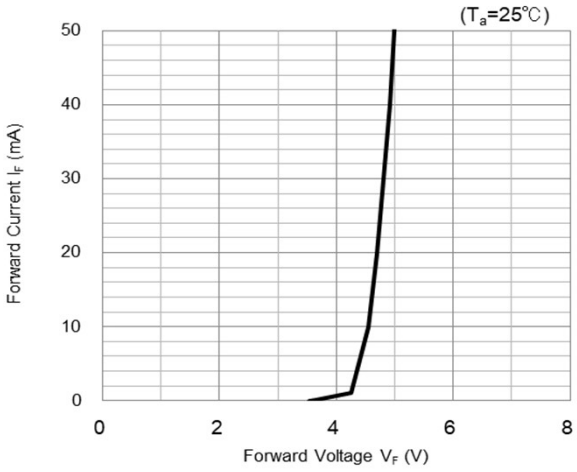
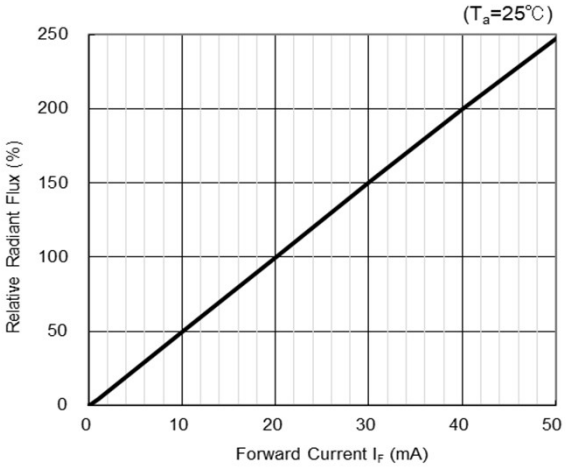
Reference Data(1)

Forward Voltage vs Forward Current



Forward Current vs Radiated Flux



Spectrum